

Serial No. 09/881,554
Docket No. DP-304198

Amendments to the Specification:

Please amend the specification by inserting the “replacement” paragraph(s) set forth below, marked up to show the changes made relative to the immediately prior version of the indicated paragraph(s).¹

Paragraph [0020] is replaced with the following replacement paragraph:

[0020] Figures 3 through 6 illustrate different applications for the joint structure 12 of Figure 1. In a circuit assembly 30 represented in Figure 3, a joint structure 32 in accordance with this invention is shown as bonding a pair of field effect transistors (FET's) 38 ~~34~~ to a conductor 42 on a ceramic substrate 40, such as beryllium oxide (BeO). In such an application, the FET's 38 ~~34~~ can be bonded to the joint structure 32, and then the assembly 30 bonded to another substrate or circuit board (not shown) with a conventional solder composition having a lower melting temperature than that of the solder used in the joint structure 32. The joint structure 32 of Figure 3 is formed of a solder-infiltrated mesh similar to the structure 12 of Figures 1 and 2, but differs by the inclusion of a jumper 36 formed by a portion of the mesh 14 that extends outside of the joint structure 32. Because it is free of solder, the jumper 36 remains flexible, allowing for its use to connect the FET's 38 ~~34~~ to a bus structure (not shown).

¹ Strikethroughs indicate deletions and underlining indicates insertions.